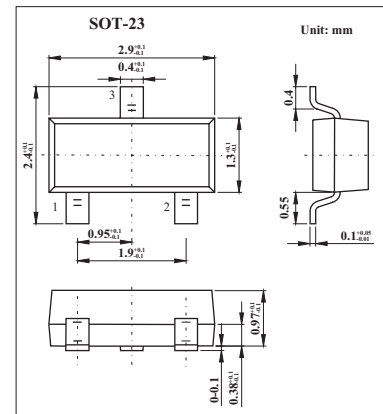


Schottky Barrier Diode

MMBD301



■ Features

■ Absolute Maximum Ratings $T_A = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Working Inverse Voltage	W_{IV}	25	V
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$	pF	200	mW
Derate above 25°C		2.0	mW/ $^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_A = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Breakdown Voltage	BV	$I_R = 10 \mu\text{A}$	30		V
Reverse Leakage	I_R	$V_R = 25 \text{V}$		200	nA
Forward Voltage	V_F	$I_F = 1.0 \text{mA}$		450	mV
		$I_F = 10 \text{mA}$		600	
Capacitance	C_T	$V_R = 15 \text{V}, f = 1.0 \text{MHz}$		1.5	pF

■ Marking

Marking	4T
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